4-Channel Differential 1:2 Mux/Demux Switch for PCI Express Gen2

The NCN2411 is a 4–Channel differential SPDT switch designed to route PCI Express Gen2 signals. When used in a PCI Express application, the switch can handle up to two PCIe lanes. Due to the ultra–low ON–state capacitance (2 pF typ) and resistance (7.5 Ω typ), this switch is ideal for switching high frequency signals up to a signal bit rate (BR) of 5 Gbps. This switch pinout is designed to be used in BTX form factor desktop PCs and is available in a space–saving 3.5 x 9 x 0.75 mm WQFN42 package.

Features

- \bullet V_{DD} Power Supply from 1.5 V to 2.0 V
- 4 Differential Channels 2:1 MUX/DEMUX
- Compatible with PCIe 2.0
- Data Rate: Supports 5 Gbps
- Low Crosstalk: -30 dB @ 3 GHz
- Low Bit-to-Bit Skew: 5 ps
- Low R_{ON} Resistance: 13 Ω max
- Low C_{ON} Capacitance: 2 pF
- Low Supply Current: 200 μA
- Insertion Loss: -2 dB @ 3 GHz
- Space Saving, Small WQFN-42 Package
- This is a Pb-Free Device

Typical Applications

- Notebook Computer
- Desktop computer
- Server/Storage Area Network

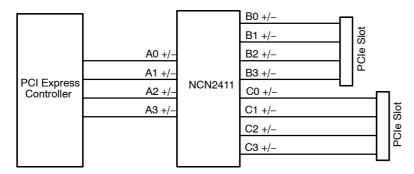


Figure 1. Application Schematic



ON Semiconductor®

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MARKING DIAGRAM

NCN2411 AWLYYWWG

WQFN42 CASE 510AP

A = Assembly Location

WL = Wafer Lot
 YY = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NCN2411MTTWG	WQFN42 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

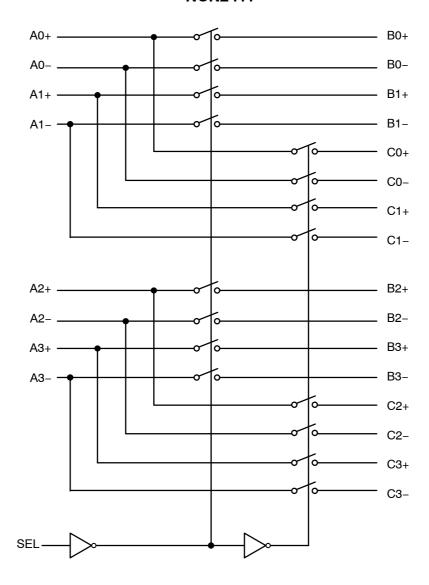


Figure 2. NCN2411 Functional Block Diagram (Top View)

TRUTH TABLE

Function	SEL
A _N to B _N	L
A _N to C _N	Н

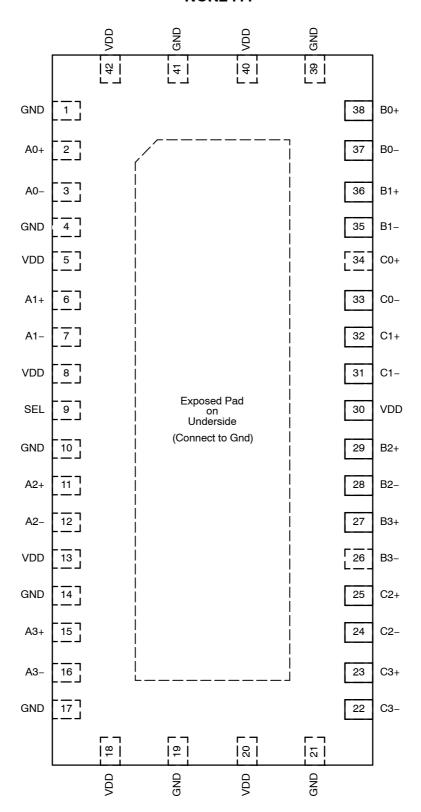


Figure 3. Pin Description (Top View)

PIN FUNCTION AND DESCRIPTION

Pin	Pin Name	Description
2, 3	A0+, A0-	Signal I/0, Channel 0, Port A
6, 7	A1+, A1-	Signal I/0, Channel 1, Port A
11, 12	A2+, A2-	Signal I/0, Channel 2, Port A
15, 16	A3+, A3-	Signal I/0, Channel 3, Port A
38, 37	B0+, B0-	Signal I/0, Channel 0, Port B
36, 35	B1+, B1-	Signal I/0, Channel 1, Port B
29, 28	B2+, B2-	Signal I/0, Channel 2, Port B
27, 26	B3+, B3-	Signal I/0, Channel 3, Port B
34, 33	C0+, C0-	Signal I/0, Channel 0, Port C
32, 31	C1+, C1-	Signal I/0, Channel 1, Port C
25, 24	C2+, C2-	Signal I/0, Channel 2, Port C
23, 22	C3+, C3-	Signal I/0, Channel 3, Port C
9	SEL	Operational Mode Select (When SEL = 0: A \rightarrow B, When SEL = 1: A \rightarrow C) Do not float this pin.
5, 8, 13, 18, 20, 30, 40, 42	VDD	DC Supply: 1.5 V to 2.0 V
1, 4, 10, 14, 17, 19, 21, 39, 41	GND	Power Ground
Exposed Pad	-	The exposed pad on the backside of package is internally connected to GND. Externally the pad should also be user-connected to GND.

MAXIMUM RATINGS

Parameter	Symbol	Rating	Units
Power Supply Voltage	V _{DD}	-0.5 to 2.5	V _{DC}
Input/Output Voltage Range of the Switch (A _N , B _N , C _N)	V _{IS}	−0.5 to V _{DD}	V _{DC}
Selection Pin Voltages	V _{SEL}	−0.5 to V _{DD}	V _{DC}
Continuous Current Through One Switch	I _{cc}	±120	mA
Maximum Junction Temperature (Note 1)	T _J	150	°C
Operating Ambient Temperature	T _A	-40 to +85	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Thermal Resistance, Junction-to-Air	$R_{ hetaJA}$	75	°C/W
Latch-up Current (Note 2)	I _{LU}	±100	mA
Human Body Model (HBM) ESD Rating (Note 3)	ESD HBM	7000	V
Machine Model (MM) ESD Rating (Note 3)	ESD MM	400	V
Moisture Sensitivity (Note 4)	MSL	Level 1	-

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded.
- Latch up Current Maximum Rating: ±100 mA per JEDEC standard: JESD78.
 This device series contains ESD protection and passes the following tests: Human Body Model (HBM) ±7.0 kV per JEDEC standard: JESD22–A114 for all pins. Machine Model (MM) ±400 V per JEDEC standard: JESD22-A115 for all pins.
- 4. Moisture Sensitivity Level (MSL): 1 per IPC/JEDEC standard: J-STD-020A.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE ($T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{DD} = 1.5$ V to 2.0 V, GND = 0V)

Symbol	Pins	Parameters	Conditions (Note 5)	Min.	Typ (Note 6)	Max.	Units
POWER S	UPPLY					I	
V_{DD}	V _{DD} , GND	Supply Voltage Range	With respect to GND	1.5	1.8	2.0	V
I _{DD}	V _{DD} , GND	Quiescent Supply Current	V_{DD} = 2 V, V_{SEL} = GND or V_{DD}		200	300	μΑ
DATA SWI	TCH PERFORM	ANCE				I	, 1
V _{IS}	A _N , B _N , C _N	Data Input/Output Voltage Range		0		1.2	V
R _{ON}	B _N	On Resistance (B _N)	$V_{DD} = 1.5 \text{ V}, V_{IS} = 0 \text{ V to } 1.2 \text{ V},$ $I_{IS} = 15 \text{ mA}$		7.5	13	Ω
R _{ON}	C _N	On Resistance (C _N)	$V_{DD} = 1.5 \text{ V}, V_{IS} = 0 \text{ V to } 1.2 \text{ V},$ $I_{IS} = 15 \text{ mA}$		8.0	13	Ω
R _{ON(flat)}	B _N	On Resistance Flatness	V_{DD} = 1.5 V, V_{IS} = 0 V to 1.2 V, I_{IS} = 15 mA (Note 7)		0.1	1.24	Ω
R _{ON(flat)}	C _N	On Resistance Flatness	$V_{DD} = 1.5 \text{ V}, V_{IS} = 0 \text{ V to } 1.2 \text{ V},$ $I_{IS} = 15 \text{ mA (Note 7)}$		0.1	1.24	Ω
ΔR_{ON}	B _N	On Resistance Matching(B _N)	V _{DD} = 1.5 V, V _{IS} = 0 V, I _{IS} = 15 mA (Note 7)			0.35	Ω
ΔR_{ON}	C _N	On Resistance Matching(C _N)	V _{DD} = 1.5 V, V _{IS} = 0 V, I _{IS} = 15 mA (Note 7)			0.35	Ω
C _{ON}	A_N to B_N , A_N to C_N	On Capacitance	f = 1 MHz, Switch On, Open Output		2.0		pF
C _{OFF}	A_N to B_N , A_N to C_N	Off Capacitance	f = 1 MHz, Switch Off		1.5		pF
I _{ON}	A_N to B_N , A_N to C_N	On Leakage Current	V_{DD} = 2 V, V_{AN} = 0 V, 1.2 V, Switch On to B_N/C_N , B_N/C_N pins are unconnected	-1		+1	μΑ
l _{OFF}	A_N to B_N , A_N to C_N	Off Leakage Current	$\begin{aligned} &V_{DD} = 2 \; V, V_{AN} = 0 \; V, 1.2 \; V, Switch \\ &Off \; to \; B_{N} / C_{N}, V_{BN} / V_{CN} = 1.2 \; V, 0 \; V \end{aligned}$	-1		+1	μΑ
LOGIC IN	PUT CHARACTE	ERISTICS (SEL Pin)					•
V _{IH}	SEL	Input HIGH Voltage	(Note 7)	0.65 x V _{DD}		V _{DD}	V
V _{IL}	SEL	Input LOW Voltage	(Note 7)	0		0.35 x V _{DD}	٧
V _{IK}	SEL	Clamp Diode Voltage	V _{DD} = Max, I _{SEL} = -18mA		-0.7	-1.2	V
I _{IH}	SEL	Input HIGH Current	$V_{DD} = Max, V_{SEL} = V_{DD}$			±5	μΑ
I _{IL}	SEL	Input LOW Current	V _{DD} = Max, V _{SEL} = GND			±5	μΑ
SWITCHIN	IG CHARACTER	RISTICS					
t _{SELON}	SEL, A _N , B _N /C _N	Line Enable Time	SEL to A_N , B_N , C_N $R_L = 50 \Omega$, $C_L = 20 pF$		8.0		ns
tseloff	SEL, A _N , B _N /C _N	Line Disable Time	SEL to A_N , B_N , C_N $R_L = 50 \Omega$, $C_L = 20 pF$		5.0		ns
t _{b-b}	$A_N, B_N/C_N$	Bit-to-bit skew	Within the same differential pair		9.0		ps
t _{ch-ch}	A _N , B _N	Channel-to channel skew	Maximum skew between all channels		50		ps

 ^{5.} For Max. or Min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.
 6. Typical values are at V_{DD} = 1.8 V, T_A = 25°C ambient and maximum loading.
 7. Guaranteed by design and/or characterization.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE ($T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{DD} = 1.5$ V to 2.0 V, GND = 0V)

Symbol	Pins	Parameters	Conditions (Note 5)	Min.	Typ (Note 6)	Max.	Units
DYNAMIC	ELECTRICAL CH	ARACTERISTICS OVER OF	PERATING RANGE				
BR	A_N to B_N , A_N to C_N	Signal Bit Rate			5.0		Gbps
D _{IL}	A_N to B_N , A_N to C_N	Differential Insertion Loss	f = 3 GHz		-2.0		dB
			f = 100 MHz		-0.7		dB
D _{CTK}	A _N , B _N , C _N	Differential Crosstalk	f = 3 GHz		-30		dB
			f = 100 MHz		-58		dB
D _{ISO}	A _N to B _N , A _N to C _N		f = 3 GHz		-23		dB
			f = 100 MHz		-58		dB
D _{RL}	A_N to B_N , A_N to C_N		f = 3 GHz		-6.0		dB
			f = 100 MHz		-22		dB

^{5.} For Max. or Min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.
6. Typical values are at V_{DD} = 1.8 V, T_A = 25°C ambient and maximum loading.
7. Guaranteed by design and/or characterization.

TYPICAL OPERATING CHARACTERISTICS

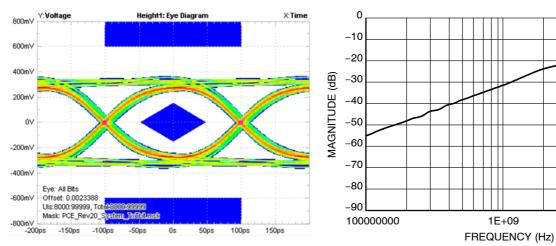


Figure 4. PCI Express Eye Diagram at 5 Gbps, 800 mVpp Differential Swing (Minimum Case)

Figure 5. Differential Off Isolation

1E+10

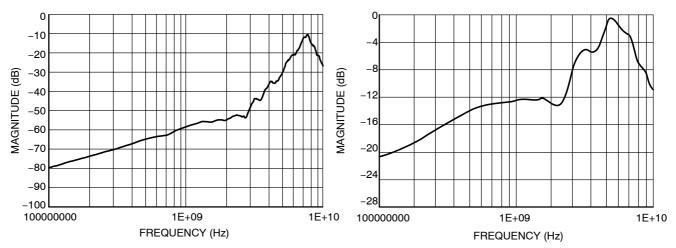


Figure 6. Differential Crosstalk

Figure 7. Differential Return Loss

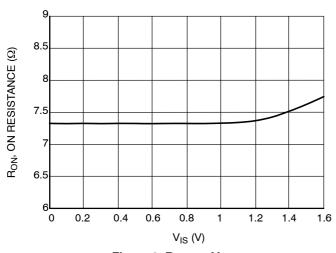


Figure 8. R_{ON} vs. V_{IS}

PARAMETER MEASUREMENT INFORMATION

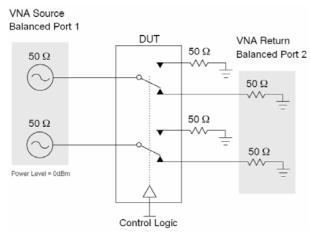
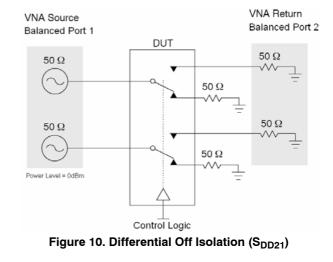


Figure 9. Differential Insertion Loss (S_{DD21}) and Differential Return Loss (S_{DD11})



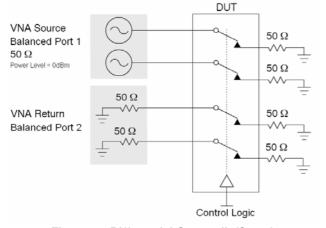


Figure 11. Differential Crosstalk (S_{DD21})

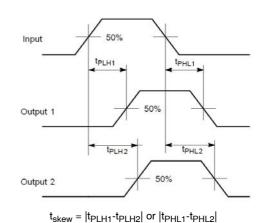
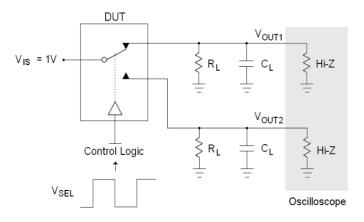


Figure 12. Bit-to-Bit and Channel-to-Channel Skew



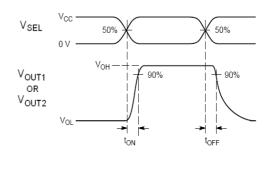


Figure 13. t_{ON} and t_{OFF}

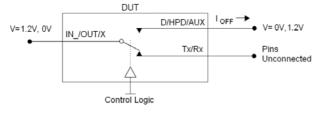


Figure 14. Off State Leakage

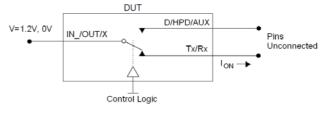


Figure 15. On State Leakage



SCALE 2:1

PIN ONE REFERENCE

0.15 C 0.15 C

0.10 C

0.08 C

⊕ 0.10 C A

42X L

42X b

А В

C NOTE 3

е

BOTTOM VIEW

e/2

0.10 С

0.05

DETAIL A

NOTE 4

WQFN42 3.5x9, 0.5P CASE 510AP **ISSUE O**

AB

Ε

D

TOP VIEW

DETAIL B

SIDE VIEW

D2>

E2

DATE 15 FEB 2010

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME
 Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION & APPLIES TO PLATED TERMINAL
- AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL TIP.
 COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIN	IETERS			
DIM	MIN	MAX			
Α	0.70	0.80			
A1	0.00	0.05			
A3					
b	0.20	0.20 REF 0.20 0.30 3.50 BSC .95 2.15 9.00 BSC			
D	3.50	BSC			
D2	1.95	2.15			
Е	9.00	BSC			
E2	7.45	7.65			
е	0.50 BSC				
K	0.20				
L	0.30	0.50			
L1	0.00	0.15			

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

= Assembly Location Α

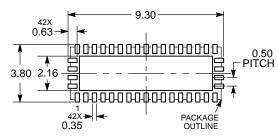
WL = Wafer Lot YY = Year

ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

RECOMMENDED MOUNTING FOOTPRINT



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DESCRIPTION:	WQFN42 3.5X9, 0.5P		PAGE 1 OF 1	

DETAIL A ALTERNATE TERMINAL CONSTRUCTIONS

DETAIL B

ALTERNATE CONSTRUCTION

MOLD CMPD

EXPOSED Cu

C SEATING

⊕ 0.10 C A B

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